

2. (Amended) The film acoustic wave device according to claim 1, wherein a length of the at least one upper electrode is changed [by] according to the position [at] where the film acoustic wave device is mounted on the wafer.

3. (Amended) The film acoustic wave device according to claim 1, wherein a width of the upper electrode is changed [by] according to the position [at] where the film acoustic wave device is mounted on the wafer.

4. (Amended) The film acoustic wave device according to claim 1[, wherein the upper electrode includes] further including a plurality of upper electrodes, wherein

distances between each of the plurality of upper electrodes are changed [by] according to the position [at] where the film acoustic wave device is mounted on the wafer.

5. (Amended) The film acoustic wave device according to claim 1 further comprising:

a bonding pad for connecting with the at least one upper electrode, wherein

~~a shape of the bonding pad is changed [by] according to the position [at] where the film acoustic wave device is mounted on the wafer.~~

6. (Amended) The film acoustic wave device according to claim 5 further comprising:

~~a connecting pattern for connecting the upper electrode with the bonding pad, wherein~~

~~a shape of the connecting pattern is changed [by] according to the position [at] where the film acoustic wave device is mounted on the wafer.~~

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8. (Amended) The film acoustic wave device according to claim 1 further comprising:

~~a capacitor provided on the same [semiconductor substrate] wafer as the film acoustic wave device, wherein~~

~~a capacitance of the capacitor is changed [by] according to the position [at] where the film acoustic wave device is mounted on the wafer.~~

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9. (Amended) The film acoustic wave device according to claim 1, wherein the [semiconductor substrate] wafer is made of gallium arsenide (GaAs)[;], the piezoelectric thin film is made of lead titanate (PbTiO₃)[;], and at least one [of the] upper electrode is a conductor substantially made of platinum (Pt).

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10. (Amended) The film acoustic wave device according to claim 1,
wherein the [a semiconductor substrate] wafer is made of silicon (Si)[;], the
piezoelectric thin film is made of lead titanate (PbTiO₃)[;], and at least one [of
the] upper electrode is a conductor substantially made of platinum (Pt).

11. (Amended) The film acoustic wave device according to claim 1,
wherein the piezoelectric thin film is made of PZT (PbTiO₃-PbZrO₃)[;], and at
least one [of the] upper electrode and the ground electrode is a conductor
substantially made of platinum (Pt).

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14. (Amended) The film acoustic wave device according to claim 1 further
comprising:
an inductor positioned between the [semiconductor substrate] wafer and
the ground electrode.

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15. (Amended) A circuit device, comprising:
a substrate; and [a plurality] of elements
at least one element formed on the substrate, wherein

[the] a pattern shape of the at least one element[s] formed on the substrate is changed [by] according to a position [at] where the circuit device is mounted on the substrate.

Please add new claim 24 as follows.

--24. The film acoustic wave device according to claim 1, wherein the wafer is a semiconductor substrate.--

REMARKS

Claims 1-24 are pending in the present application. Claims 1-6, 8-11, 14 and 15 have been amended. Claim 24 has been added. Claims 1, 15 and 16 are independent.

Applicants respectfully submit that claims 1-6, 8-11, 14 and 15 have been amended in order to more clearly recite the features of the present invention and to ensure compliance with 35 U.S.C. §112(2).

RESTRICTION REQUIREMENT

In the Office Action dated January 27, 2000, the Examiner required restriction between Group I, including claims 1-15, drawn to a film acoustic wave device, classified in Class 310, Subclass 334; and Group II, including